

# STARPOWER

SEMICONDUCTOR

**IGBT**

## GD450HFT120C2S\_G8

**1200V/450A 2 in one-package**

### General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverter and UPS.

### Features

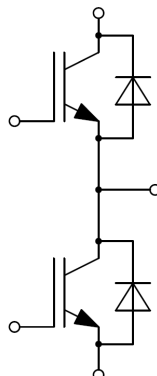
- Low  $V_{CE(sat)}$  Trench IGBT technology
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175 $^{\circ}$ C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



### Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

### Equivalent Circuit Schematic



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	685	A
	@ $T_C=95^{\circ}\text{C}$	450	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	900	A
$P_D$	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	2206	W

**Diode**

Symbol	Description	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$I_F$	Diode Continuous Forward Current	450	A
$I_{FM}$	Diode Maximum Forward Current $t_p=1\text{ms}$	900	A

**Module**

Symbol	Description	Value	Unit
$T_{jmax}$	Maximum Junction Temperature	175	$^{\circ}\text{C}$
$T_{jop}$	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
$V_{ISO}$	Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$	4000	V

**IGBT Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V
		$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95		
		$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=18.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	5.6	6.5	V
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA
$R_{Gint}$	Internal Gate Resistance			0.7		$\Omega$
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		39.0		nF
$C_{res}$	Reverse Transfer Capacitance			1.26		nF
$Q_G$	Gate Charge	$V_{GE}=15\text{V}$		2.46		$\mu\text{C}$
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=450\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		360		ns
$t_r$	Rise Time			140		ns
$t_{d(off)}$	Turn-Off Delay Time			550		ns
$t_f$	Fall Time			146		ns
$E_{on}$	Turn-On Switching Loss			11.5		mJ
$E_{off}$	Turn-Off Switching Loss			48.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=450\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		374		ns
$t_r$	Rise Time			147		ns
$t_{d(off)}$	Turn-Off Delay Time			623		ns
$t_f$	Fall Time			178		ns
$E_{on}$	Turn-On Switching Loss			17.9		mJ
$E_{off}$	Turn-Off Switching Loss			64.5		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=450\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		381		ns
$t_r$	Rise Time			152		ns
$t_{d(off)}$	Turn-Off Delay Time			636		ns
$t_f$	Fall Time			184		ns
$E_{on}$	Turn-On Switching Loss			19.6		mJ
$E_{off}$	Turn-Off Switching Loss			69.0		mJ
$I_{SC}$	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		1800		A

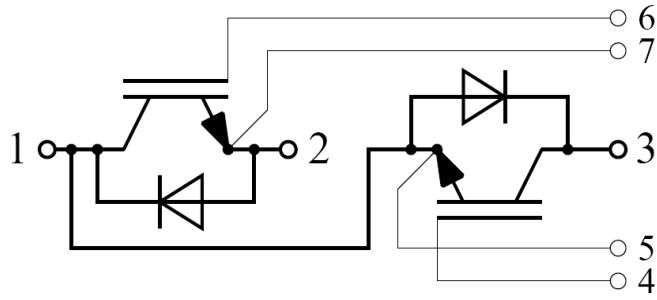
**Diode Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.72	2.12	V
		$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.73		
		$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.74		
$Q_r$	Recovered Charge			40.3		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=450\text{A},$ $-di/dt=3000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=25^\circ\text{C}$		258		A
$E_{rec}$	Reverse Recovery Energy			19.0		mJ
$Q_r$	Recovered Charge			71.9		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=450\text{A},$ $-di/dt=3000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=125^\circ\text{C}$		338		A
$E_{rec}$	Reverse Recovery Energy			39.1		mJ
$Q_r$	Recovered Charge			79.3		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=450\text{A},$ $-di/dt=3000\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=150^\circ\text{C}$		352		A
$E_{rec}$	Reverse Recovery Energy			41.8		mJ

**Module Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

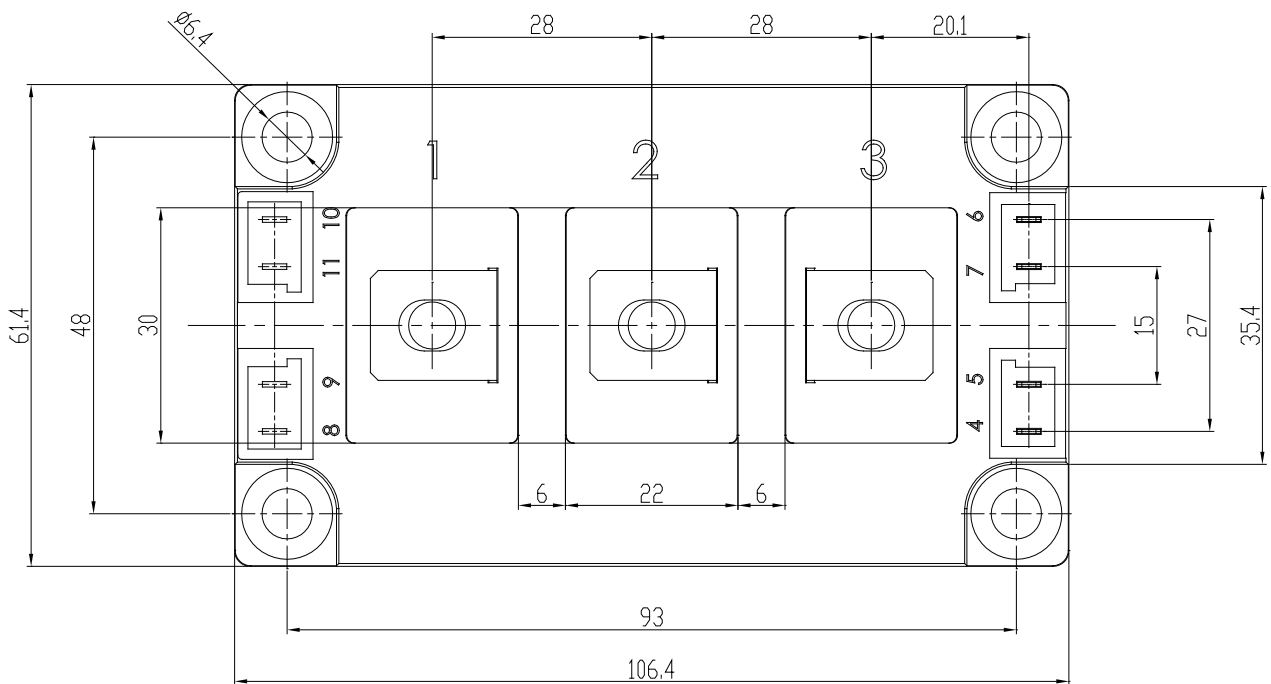
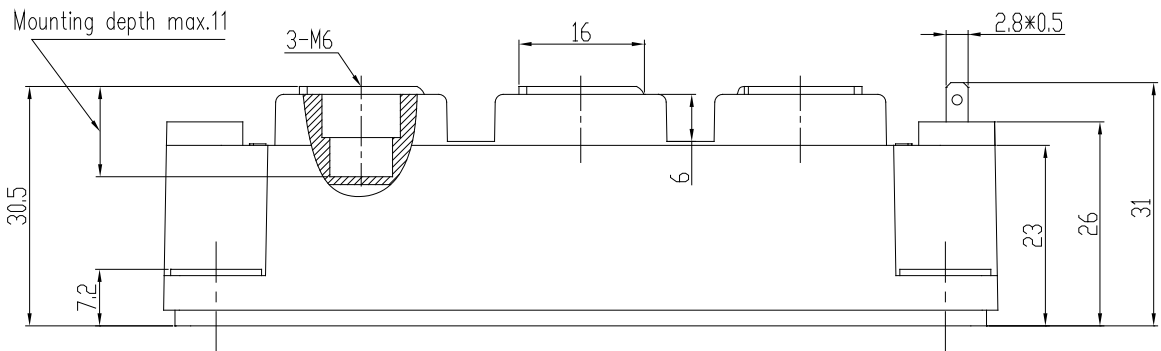
Symbol	Parameter	Min.	Typ.	Max.	Unit
$L_{CE}$	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m $\Omega$
$R_{\theta JC}$	Junction-to-Case (per IGBT)			0.068	K/W
	Junction-to-Case (per Diode)			0.117	
$R_{\theta CS}$	Case-to-Sink (per IGBT)		0.111		K/W
	Case-to-Sink (per Diode)		0.190		
$R_{\theta CS}$	Case-to-Sink		0.035		K/W
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

**Circuit Schematic**



**Package Dimensions**

Dimensions in Millimeters



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